

Substitute for form 1449A&B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/757,770
				Filing Date	January 14, 2004
				First Named Inventor	Yuan, Zheng
				Art Unit	1792
Examiner Name	Kelly M. Stouffer				
Sheet	1	of	7	Attorney Docket Number	016301-052200US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number <small>Number Kind Code² (if known)</small>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-2,861,009	11-01-1958	Rubner	
	AB	US-2,889,704	08-01-1959	Pekarek	
	AC	US-2001-0019860	09-06-2001	Adachi et al.	
	AD	US-2002-0000195	01-03-2002	Bang et al.	
	AE	US-2002-0000196	01-03-2002	Park	
	AF	US-2002-0004282	01-10-2002	Hong	
	AG	US-2002-0007790	01-24-2002	Park	
	AH	US-2002-0011215	01-31-2002	Tel et al.	
	AI	US-2002-0006729	01-2002	Geiger et al.	
	AJ	US-2002-0102358	08-01-2002	Das et al.	
	AK	US-2002-0168840 A1	11-14-2002	Hong et al.	
	AL	US-2002-0192370	12-19-2002	Metzner et al.	
	AM	US-2003-0019428	01-01-2003	Ku et al.	
	AN	US-2003-0022523	01-01-2003	Irimo et al.	
	AO	US-2003-0054670	03-20-2003	Wang et al.	
	AP	US-2003-0057432	03-27-2003	Gardner et al.	
	AQ	US-2003-0071304	04-17-2003	Ogie, Jr., et al.	
	AR	US-2003-0073290	04-17-2003	Ramkumar et al.	
	AS	US-2003-0089314	05-01-2003	Matsuki et al.	
	AT	US-2003-0104677	06-01-2003	Park et al.	
	AU	US-2003-0111961	06-01-2003	Katz et al.	
	AV	US-2003-0138562	07-2003	Subramony et al.	
	AW	US-2003-0168006	09-01-2003	Williams	
	AX	US-2003-0201723	10-01-2003	Katz et al.	
	AY	US-2003-0207530 A1	11-06-2003	Yu et al.	
	AZ	US-2003-0209323	11-01-2003	Yokogaki	
	BA	US-2004-0003873 A1	01-08-2004	Chen et al.	
	BB	US-2004-0018699	01-29-2004	Boyd et al.	
	BC	US-2004-0060514	04-01-2004	Janakiraman et al.	
	BD	US-2004-0200499	10-01-2004	Harvey et al.	
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	BE	US-2004-0216844	11-01-2004	Janakiraman et al.	
	BF	US-2004-0224537	11-01-2004	Lee et al.	
	BG	US-2005-0064730 A1	03-24-2005	Ingle et al.	
	BH	US-2005-0186755	08-25-2005	Smythe et al.	
	BI	US-2006-0030165	02-09-2006	Ingle et al.	
	BJ	US-2006-0046427	03-02-2006	Ingle et al.	
	BK	US-2006-0148273 A1	07-06-2006	Ingle et al.	
	BL	US-3,046,177	07-01-1962	Hankins	
	BM	US-3,048,888	08-01-1962	Shockley et al.	
	BN	US-3,109,703	11-01-1963	Politzer et al.	
	BO	US-3,142,714	07-01-1964	Politzer et al.	
	BP	US-3,166,454	01-01-1965	Voelker	
	BQ	US-4,297,162	10-27-1981	Mundt et al.	
	BR	US-4,590,042	05-20-1986	Drage	
	BS	US-4,732,761	03-22-1988	Machida et al.	
	BT	US-4,792,378	12-20-1988	Rose et al.	
	BU	US-4,854,263	08-08-1989	Chang et al.	
	BV	US-4,892,753	01-09-1990	Wang et al.	
	BW	US-4,962,063	10-09-1990	Maydan et al.	
	BX	US-4,989,541	02-01-1991	Mikoshiba et al.	
	BY	US-5,089,442	02-18-1992	Olmer	
	BZ	US-5,124,014	06-23-1992	Foo et al.	
	CA	US-5,204,288	04-20-1993	Marks et al.	
	CB	US-5,244,841	09-14-1993	Marks et al.	
	CC	US-5,264,040	11-01-1993	Geyling et al.	
	CD	US-5,356,722	10-18-1994	Nguyen et al.	
	CE	US-5,439,524	08-08-1995	Cain et al.	
	CF	US-5,474,955	12-12-1995	Thakur, Randhir P. S.	
	CG	US-5,492,858	02-01-1996	Bose et al.	
	CH	US-5,567,267	10-01-1996	Kazama et al.	
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		Number Kind Code ² (if known)			
	CI	US-5,589,002	12-31-1996	Su	
	CJ	US-5,597,439	01-28-1997	Salzman	
	CK	US-5,660,472	08-26-1997	Peuse et al.	
	CL	US-5,710,079	01-20-1998	Sukharev	
	CM	US-5,728,223	03-01-1998	Murakami et al.	
	CN	US-5,728,260	03-17-1998	Brown et al.	
	CO	US-5,789,322	08-04-1998	Brown et al.	
	CP	US-5,807,785	09-15-1998	Ravi	
	CQ	US-5,812,403	09-01-1998	Fong et al.	
	CR	US-5,840,631	11-24-1998	Kubo et al.	
	CS	US-5,939,763	08-17-1999	Hao et al.	
	CT	US-5,976,261	11-02-1999	Mostehi et al.	
	CU	US-5,980,686	11-09-1999	Goto	
	CV	US-6,001,175	12-14-1999	Maruyama et al.	
	CW	US-6,024,799	02-01-2000	Chen et al.	
	CX	US-6,043,136	03-28-2000	Jang et al.	
	CY	US-6,050,506	04-18-2000	Guo et al.	
	CZ	US-6,079,353	06-27-2000	Leksel et al.	
	DA	US-6,079,356	06-01-2000	Umotoy et al.	
	DB	US-6,099,647 A	8-2000	Yieh et al.	
	DD	US-6,106,663	08-01-2000	Kuthi et al.	
	DC	US-6,106,678	08-22-2000	Shufflebotham et al.	
	DE	US-6,133,160 A	10-2000	Komiyama et al.	
	DF	US-6,136,685	10-24-2000	Narwankar et al.	
	DG	US-6,140,242	10-31-2000	Oh et al.	
	DH	US-6,149,987	11-21-2000	Perng et al.	
	DI	US-6,150,209	11-21-2000	Sun et al.	
	DJ	US-6,150,286	11-21-2000	Sun et al.	
	DK	US-6,156,114	12-05-2000	Bell et al.	
	DL	US-6,171,901	01-09-2001	Blair et al.	
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	DM	US-6,184,155	02-06-2001	Yu et al.	
	DN	US-6,190,973	02-20-2001	Berg et al.	
	DO	US-6,194,038	02-27-2001	Rossman	
	DP	US-6,197,705	03-06-2001	Vassiliev	
	DQ	US-6,203,863	03-20-2001	Liu et al.	
	DR	US-6,206,972	03-27-2001	Dunham	
	DS	US-6,217,658	04-17-2001	Orczyk et al.	
	DT	US-6,232,580	05-15-2001	Sandhu	
	DU	US-6,239,002	05-29-2001	Jang et al.	
	DV	US-6,245,192	06-12-2001	Lenz et al.	
	DW	US-6,245,689	06-12-2001	Hao et al.	
	DX	US-6,248,397	06-01-2001	Ye	
	DY	US-6,248,628	06-19-2001	Halliyal et al.	
	DZ	US-6,267,074	07-31-2001	Okumura	
	EA	US-6,276,072	08-21-2001	Morad et al.	
	EB	US-6,302,965	10-16-2001	Umotoy et al.	
	EC	US-6,319,849 B1	11-2001	Oda et al.	
	ED	US-6,331,494	12-18-2001	Olson et al.	
	EE	US-6,337,256	01-08-2002	Shim	
	EF	US-6,340,435	01-22-2002	Bjorkman et al.	
	EG	US-6,348,421	02-19-2002	Shu et al.	
	EH	US-6,436,193	08-20-2002	Kasai et al.	
	EI	US-6,444,039	09-01-2002	Nguyen et al.	
	EJ	US-6,454,860	09-24-2002	Metzner et al.	
	EK	US-6,468,853 B1	10-22-2002	Balasubramanian et al.	
	EL	US-6,475,284	11-05-2002	Moore et al.	
	EM	US-6,479,405	11-12-2002	Lee et al.	
	EN	US-6,512,264	01-28-2003	Ogie, Jr., et al.	
	EO	US-6,527,910	03-04-2003	Rossman	
	EP	US-6,541,367	04-01-2003	Mandal	
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		Number Kind Code ² (if known)			
	EQ	US-6,541,401	04-01-2003	Herner et al.	
	ER	US-6,565,661	05-20-2003	Nguyen et al.	
	ES	US-6,583,069 B1	6-2003	Vassilev et al.	
	ET	US-6,586,886	07-01-2003	Katz et al.	
	EU	US-6,602,792	08-01-2003	Hsu, Shu-Ya	
	EV	US-6,617,259 B1	09-2003	Jung et al.	
	EW	US-6,624,091	09-26-2003	Yuan	
	EX	US-6,677,712	01-01-2004	Katz et al.	
	EY	US-6,713,127 B2	03-30-2004	Subramony et al.	
	EZ	US-6,733,955	05-11-2004	Geiger et al.	
	FA	US-6,734,115	05-11-2004	Cheung et al.	
	FB	US-6,740,601	05-25-2004	Tan et al.	
	FC	US-6,793,733	09-01-2004	Janakiraman et al.	
	FD	US-6,830,624	12-14-2004	Janakiraman et al.	
	FE	US-6,875,558	04-05-2005	Gaillard et al.	
	FF	US-6,905,940	06-14-2005	Ingle et al.	
	FG	US-6,943,091	09-13-2005	Yu et al.	
	FH	US-6,946,358	09-01-2005	Doris et al.	
	FI	US-6,949,447	09-01-2005	Ahn et al.	
	FJ	US-7,037,859	05-02-2006	Ingle et al.	
	FK	US-7,141,483 B2	11-28-2006	Yuan et al.	
	FL	US-7,208,425	04-24-2007	Ingle et al.	
	FM	US-7,335,609 B2	02-26-2008	Ingle et al.	

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		Country Code ³	Number ⁴ Kind Code ⁵ (if known)				
	FN	CA	479107	12-04-1951	Goodrich Co.		<input type="checkbox"/>
	FO	EP	0520519 A1	12-30-1992	Applied Materials, Inc.		<input type="checkbox"/>
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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
	FP	JP	01283375	A	11-14-1989	Fujitsu Ltd.		<input type="checkbox"/>
	FQ	JP	01294868	A	11-28-1989	Nippon Electric Co. et al.		<input type="checkbox"/>
	FR	JP	4154116	A	05-27-1992	Fujitsu		<input type="checkbox"/>
	FS	JP	11176593	A	07-02-1999	Canon inc.		<input type="checkbox"/>
	FT	TW	479315	A	03-11-2002	Applied Materials, Inc.		<input type="checkbox"/>
	FU	WO	9925895	A1	05-27-1999	Symetrix Corp.		<input type="checkbox"/>

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	FV	Applied Materials Website Printout: "SACVD (Sub-Atmospheric Chemical Vapor Deposition)" from www.appliedmaterials.com/products/sacvd.html , printed 06/20/2003.	<input type="checkbox"/>
	FW	BAKER, F. et al. "STI TEOS Densification for Furnaces and RTP Tools" 1999 IEEE/SEMI Advanced Semiconductor Manufacturing Conference, 1999, pp. 394-399.	<input type="checkbox"/>
	FX	Bang et al. (Jan. 3, 2002). US Patent Application Publication US-2002-0000195 A1.	<input type="checkbox"/>
	FY	Definitions of "furnace", Merriam-Webster Online, 2006	<input type="checkbox"/>
	FZ	Fujino, K. et al., "Dependence Of Deposition Characteristics On Base Materials In TEOS And Ozone CVD At Atmospheric Pressure," J. Electrochem. Soc., Vol. 138, No. 2, pp. 550-554, February 1991	<input type="checkbox"/>

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	GA	Kuo, Yue, "Etch Mechanism In The Low Refractive Index Silicon Nitride Plasma-Enhanced Chemical Vapor Deposition Process," Appl. Phys. Lett., Vol. 63, No. 2, pp. 144-146, July 12, 1993	<input type="checkbox"/>
	GB	Kwok, K. et al., "Surface Related Phenomena In Integrated PECVD/Ozone-TEOS SACVD Processes For Sub-Half Micron Gap Fill: Electrostatic Effects," J. Electrochem. Soc., Vol. 141, No. 8, pp. 2172-2177, August 1994	<input type="checkbox"/>
	GC	Lassig, Stephan E. et al., "Intermetal Dielectric Deposition By Electron Cyclotron Resonance Chemical Vapor Deposition (ECR CVD)," pp. cover and 1-21, no date	<input type="checkbox"/>
	GD	Li, Junling et al., "Modeling Studies Of The Mechanisms In Biased ECR CVD," 3 pages, no date	<input type="checkbox"/>
	GE	Machida, Katsuyuki et al., "SiO2 Planarization Technology With Biasing And Electron Cyclotron Resonance Plasma Deposition For Submicron Interconnections," J Vac. Sci. Technol. B, Vol. 4, No. 4, pp. 818-821, July/August 1986	<input type="checkbox"/>

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